## 1. General description

NPN low  $V_{\text{CEsat}}$  Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP complement: PBSS5160QA.

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	60	V
I <sub>C</sub>	collector current		-	-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	1.5	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 1 A; $I_B$ = 0.1 A; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	170	235	mΩ



60 V, 1 A NPN low VCEsat (BISS) transistor

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	В	base		C	
2	Е	emitter		В	
3	С	collector	4 3	- 1	
4	С	collector	2	2	E sym123
			Transparent top view DFN1010D-3 (SOT1215)		

# 6. Ordering information

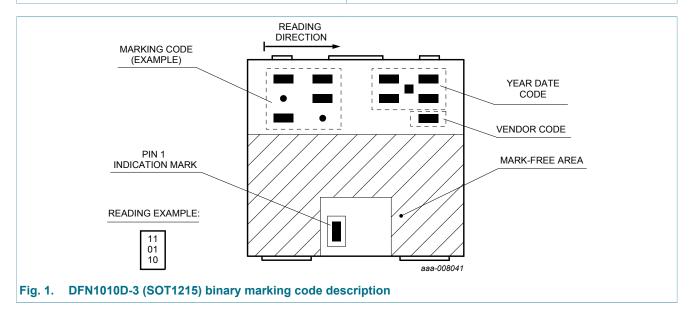
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4160QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4160QA	11 00 10



PBSS4160QA

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60 V, 1 A NPN low VCEsat (BISS) transistor

## 8. Limiting values

Table 5. Limiting values

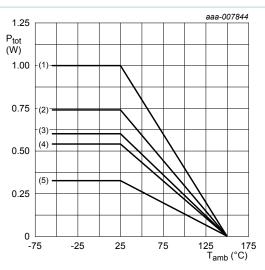
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	60	V
$V_{CEO}$	collector-emitter voltage	open base		-	60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	1.5	Α
I <sub>B</sub>	base current			-	0.3	Α
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			<u>[5]</u>	-	1000	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

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### 60 V, 1 A NPN low VCEsat (BISS) transistor



- (1) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>
- (2) FR4 PCB, single-sided copper, 6 cm<sup>2</sup>
- (3) FR4 PCB, single-sided copper, 1 cm<sup>2</sup>
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided copper, standard footprint

Fig. 2. Power derating curves

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> ther	thermal resistance	in free air	[1]	-	-	385	K/W
	from junction to ambient		[2]	-	-	209	K/W
ambient	anibient		[3]	-	-	169	K/W
			[4]	-	-	232	K/W
			[5]	-	-	125	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

60 V, 1 A NPN low VCEsat (BISS) transistor

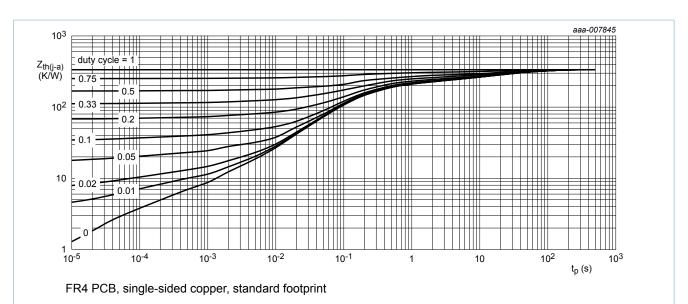


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

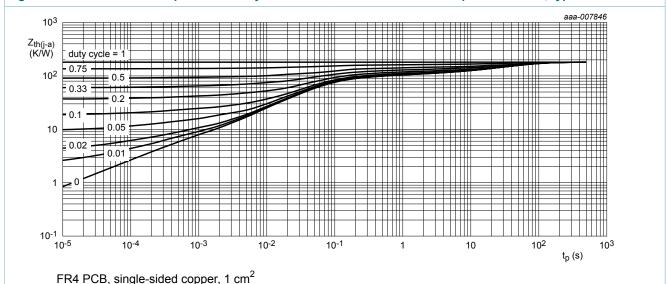


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 1 A NPN low VCEsat (BISS) transistor

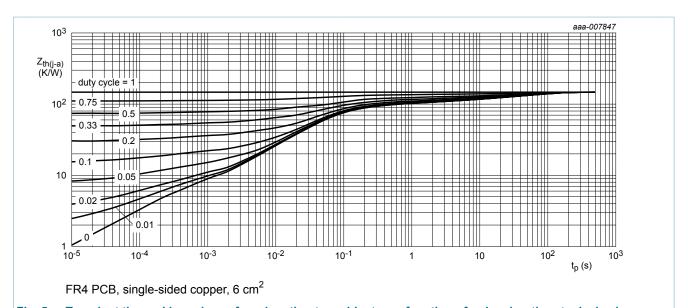


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

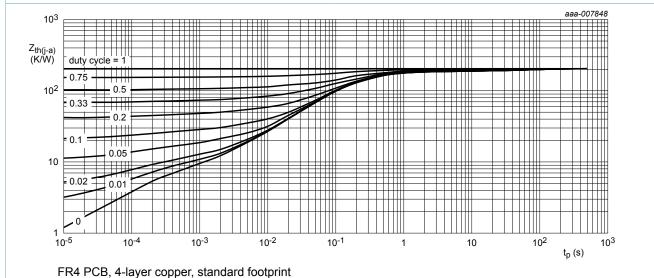
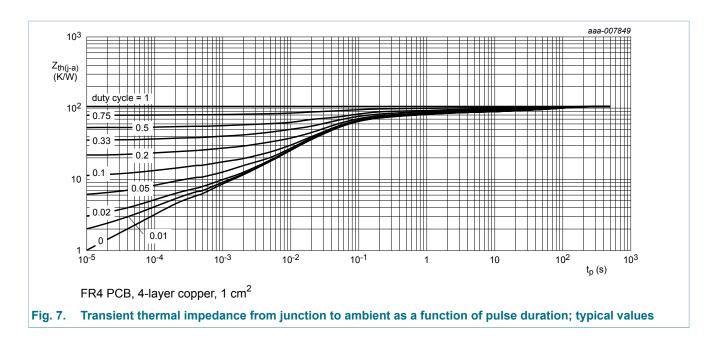


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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60 V, 1 A NPN low VCEsat (BISS) transistor



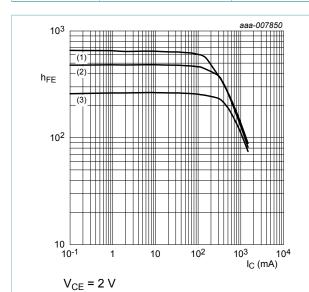
### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 48 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; $I_{C}$ = 100 mA; pulsed; $t_{p} \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	230	400	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	150	240	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	85	130	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 500 mA; $I_B$ = 50 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	90	125	mV
		$I_C$ = 1 A; $I_B$ = 50 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	-	180	245	mV
		$I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb}$ = 25 °C	-	170	235	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 1 A; $I_B$ = 0.1 A; pulsed; $t_p \le 300 \ \mu s$ ; $δ \le 0.02$ ; $T_{amb}$ = 25 °C	-	170	235	mΩ

### 60 V, 1 A NPN low VCEsat (BISS) transistor

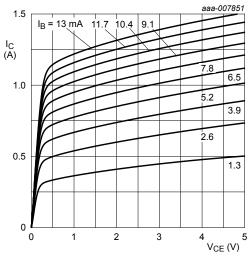
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>BEsat</sub> base-emitte voltage	base-emitter saturation voltage	$I_{C}$ = 500 mA; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.89	1	V
		$I_{C}$ = 1 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.94	1.05	V
		$I_{C}$ = 1 A; $I_{B}$ = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.98	1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = 2 V; $I_{C}$ = 0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.78	0.9	V
t <sub>d</sub>	delay time	$V_{CC}$ = 10 V; $I_{C}$ = 0.5 A; $I_{Bon}$ = 25 mA; $I_{Boff}$ = -25 mA; $T_{amb}$ = 25 °C	-	15	-	ns
t <sub>r</sub>	rise time		-	85	-	ns
t <sub>on</sub>	turn-on time		-	100	-	ns
t <sub>s</sub>	storage time	_	-	545	-	ns
t <sub>f</sub>	fall time		-	125	-	ns
t <sub>off</sub>	turn-off time		-	670	-	ns
f⊤	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	120	180	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	4.7	6	pF



(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 8. DC current gain as a function of collector current; typical values

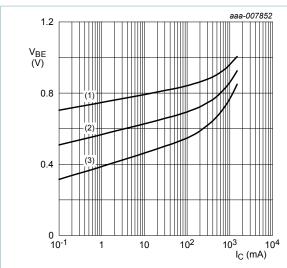


 $T_{amb}$  = 25 °C

Fig. 9. Collector current as a function of collectoremitter voltage; typical values

<sup>(2)</sup>  $T_{amb} = 25 \, ^{\circ}C$ 

### 60 V, 1 A NPN low VCEsat (BISS) transistor



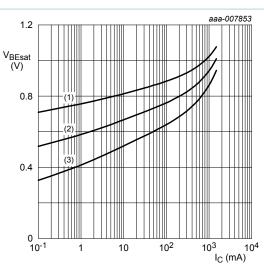
$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 10. Base-emitter voltage as a function of collector current; typical values



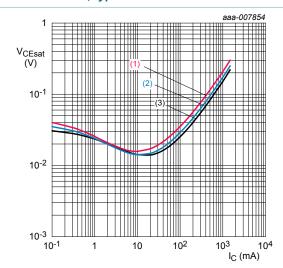
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values



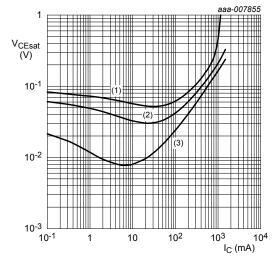
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values



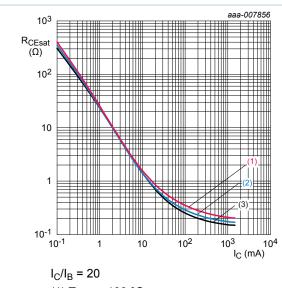
(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values

### 60 V, 1 A NPN low VCEsat (BISS) transistor

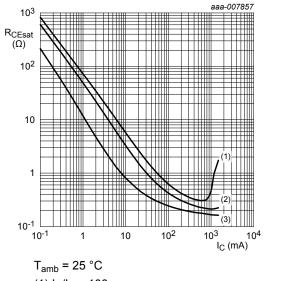


(1) 
$$T_{amb}$$
 = 100 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values



(1) 
$$I_C/I_B = 100$$

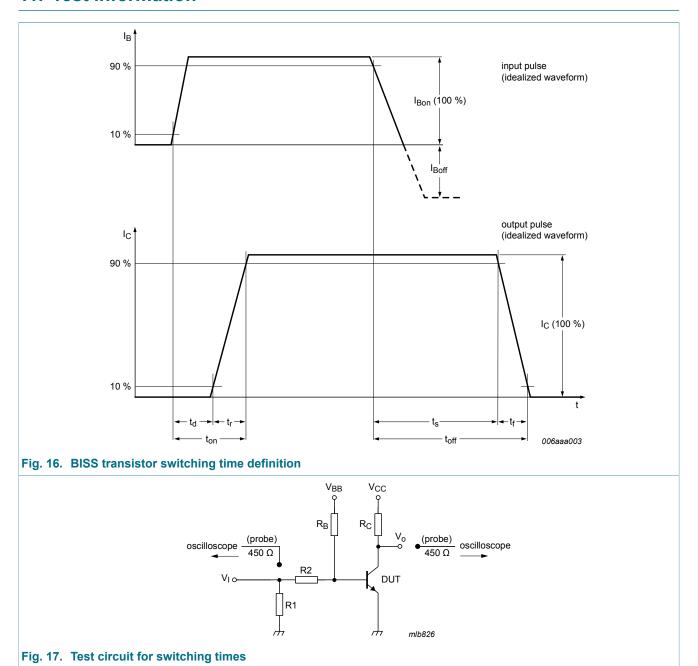
(2) 
$$I_{\rm C}/I_{\rm B} = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

60 V, 1 A NPN low VCEsat (BISS) transistor

### 11. Test information

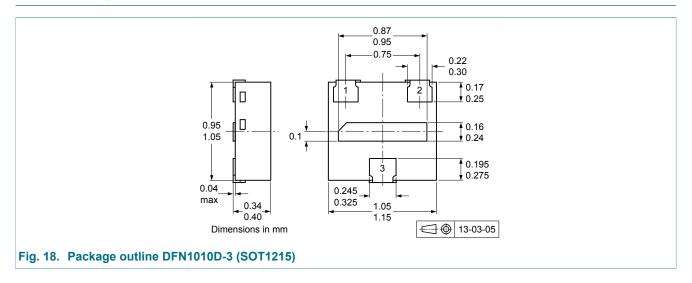


### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

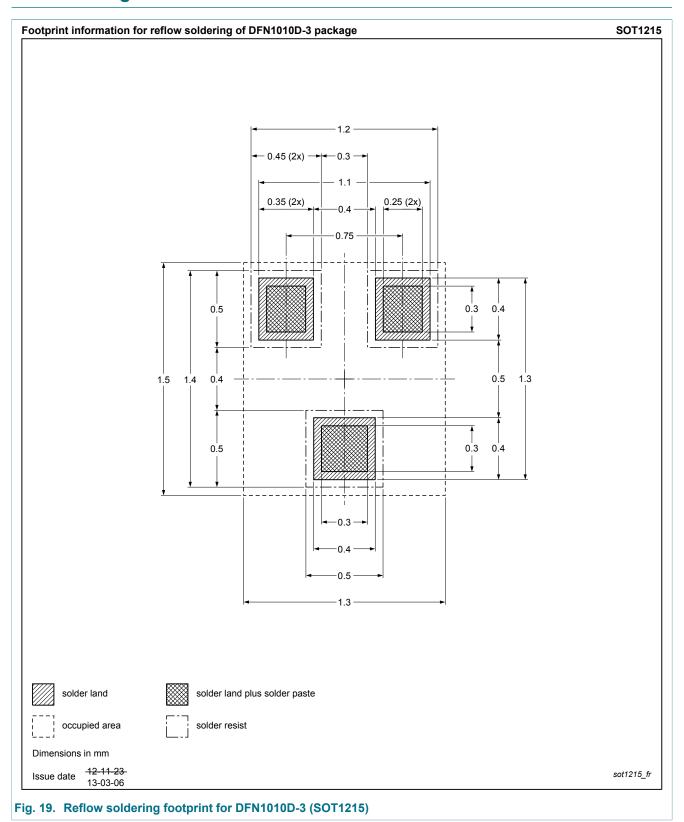
60 V, 1 A NPN low VCEsat (BISS) transistor

# 12. Package outline



60 V, 1 A NPN low VCEsat (BISS) transistor

## 13. Soldering



PBSS4160QA

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60 V, 1 A NPN low VCEsat (BISS) transistor

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4160QA v.1	20130823	Product data sheet	-	-

#### 60 V, 1 A NPN low VCEsat (BISS) transistor

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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60 V, 1 A NPN low VCEsat (BISS) transistor

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